NSN 5961-01-206-4436

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-206-4436 **Inclosure Material:** Ceramic **Overall Length:** Between 0.690 inches and 0.770 inches **Overall Height:** Between 0.105 inches and 0.175 inches Overall Width: Between 0.290 inches and 0.325 inches **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 100.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source all transistor and 20.0 gate to source voltage all transistor **Power Rating Per Characteristic:** 1.4 watts total power dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 14 pin **Specification Data:** 81349-mil-prf-19500/598 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.